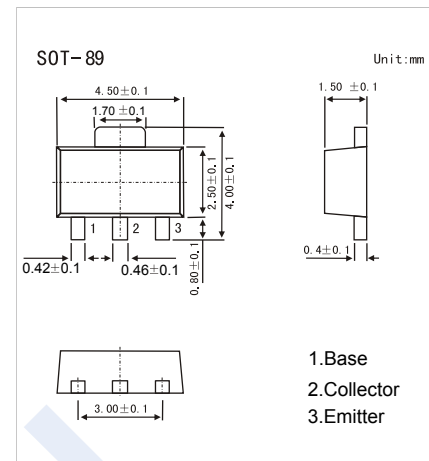


NPN Transistors

2SC2880

■ Features

- High Voltage: $V_{CE0}=150V$
- High Transition Frequency
- Small Flat Package
- Complementary to 2SA1200



■ Absolute Maximum Ratings $T_a = 25^\circ C$

Parameter	Symbol	Rating	Unit
Collector - Base Voltage	V_{CBO}	200	V
Collector - Emitter Voltage	V_{CEO}	150	
Emitter - Base Voltage	V_{EBO}	5	
Collector Current - Continuous	I_C	50	mA
Base Current	I_B	10	
Collector Power Dissipation (Note.1)	P_C	500 800	mW
Junction Temperature	T_J	150	
Storage Temperature Range	T_{stg}	-55 to 150	

Note.1: Mounted on ceramic substrate(250mm²X0.8t)

■ Electrical Characteristics $T_a = 25^\circ C$

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector- base breakdown voltage	V_{CBO}	$I_C = 100 \mu A, I_E = 0$	200			V
Collector- emitter breakdown voltage	V_{CEO}	$I_C = 1 mA, I_B = 0$	150			
Emitter - base breakdown voltage	V_{EBO}	$I_E = 100 \mu A, I_C = 0$	5			
Collector-base cut-off current	I_{CBO}	$V_{CB} = 200V, I_E = 0$			0.1	μA
Emitter cut-off current	I_{EBO}	$V_{EB} = 5V, I_C = 0$			0.1	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = 10 mA, I_B = 1 mA$			0.5	V
Base - emitter saturation voltage	$V_{BE(sat)}$	$I_C = 10 mA, I_B = 1 mA$			1.2	
Base - emitter voltage	V_{BE}	$V_{CE} = 5V, I_C = 30 mA$			1	
DC current gain	h_{FE}	$V_{CE} = 5V, I_C = 10 mA$	70		240	
Collector output capacitance	C_{ob}	$V_{CB} = 10V, I_E = 0, f = 1 MHz$		3.5	5	μF
Transition frequency	f_T	$V_{CE} = 30V, I_C = 10 mA$		120		MHz

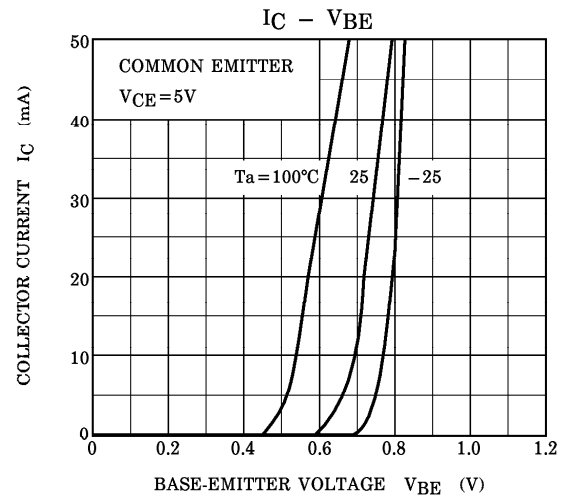
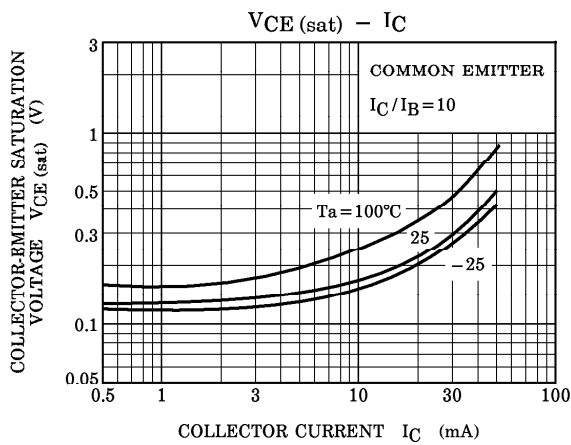
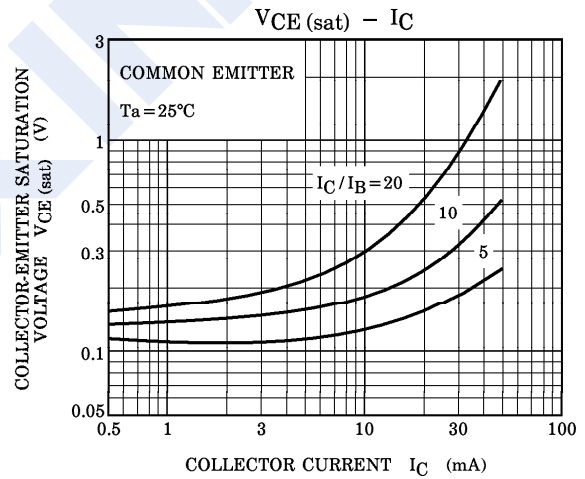
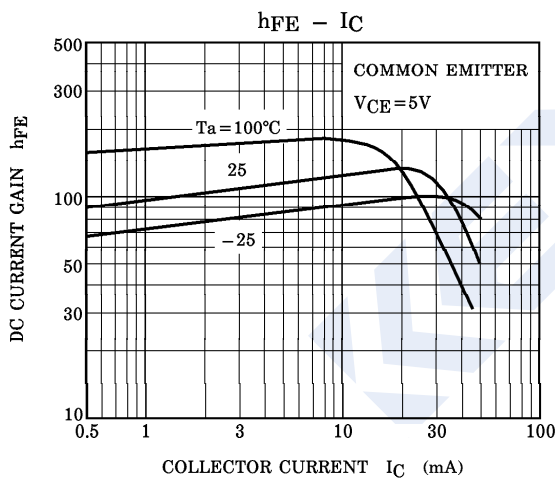
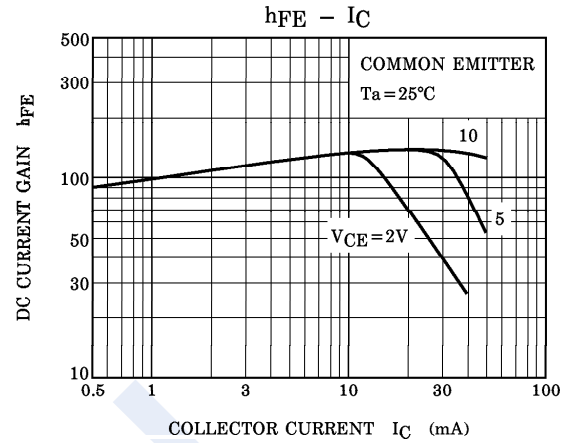
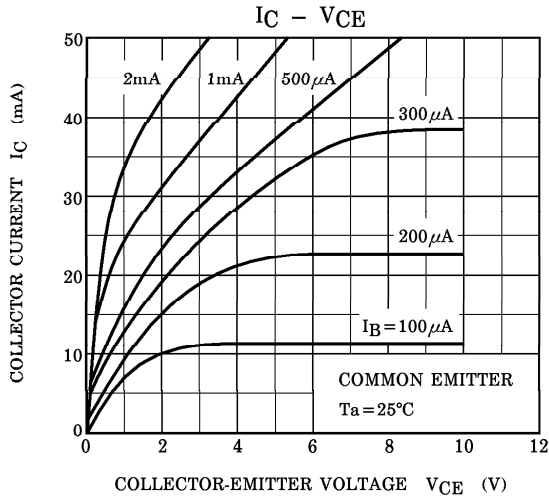
■ Classification of h_{FE}

Type	2SC2880-O	2SC2880-Y
Range	70-140	120-240
Marking	AO	AY

NPN Transistors

2SC2880

■ Typical Characteristics



NPN Transistors

2SC2880

■ Typical Characteristics

